

SANYO	No.397E	<h2 style="margin: 0;">2SB514/2SD330</h2> <p style="margin: 0;">PNP/NPN Triple Diffused Planar Silicon Transistors</p> <p style="margin: 0;">50V/2A Low-Frequency Power Amp Applications</p>
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Features

- Especially suited for use in output stage of 10W AF Power amp
- Complementary pair with the 2SB514 and 2SD313

() : 2SB514

Absolute Maximum Ratings at Ta = 25°C

Collector-to-Base Voltage	V _{CB0}	(-)50	V
Collector-to-Emitter Voltage	V _{CE0}	(-)50	V
Emitter-to-Base Voltage	V _{EBO}	(-)5	V
Collector Current	I _C	(-)2	A
Collector Current (Pulse)	I_{CP}	(-)5	A
Collector Dissipation	P _C	1.75	W
		T _C = 25°C	
Junction Temperature	T _j	20	W
Storage Temperature	T _{stg}	150	°C
		-55 to +150	°C

Electrical Characteristics at Ta = 25°C

			min	typ	max	unit
Collector Cutoff Current	I _{CBO}	V _{CB} = (-)20V, I _E = 0			(-)0.1	mA
Emitter Cutoff Current	I _{EBO}	V _{EB} = (-)4V, I _C = 0			(-)1.0	mA
DC Current Gain	h _{FE} (1)	V _{CE} = (-)2V, I _C = (-)1A	40*		320*	
	h _{FE} (2)	V _{CE} = (-)2V, I _C = (-)0.1A	35			
Gain-Bandwidth Product	f _T	V _{CE} = (-)5V, I _C = (-)0.5A		8		MHz
C-E Saturation Voltage	V _{CE(sat)}	I _C = (-)2A, I _B = (-)0.2A		(-)1.0		V
Base-to-Emitter Voltage	V _{BE}	I _C = (-)1A, V _{CE} = (-)5V		(-)1.5		V

* The 2SB514/2SD330 are classified by 1A h_{FE} as follows

40	C	80	60	D	120	100	E	200	160	F	320
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Package Dimensions 2010B

(unit: mm)





